

SN74LVC165A 8-Bit Parallel-Load Shift Registers

1 Features

- Operating range from 1.1V to 3.6V
- Over-voltage tolerant inputs support up to 5.5V independent of V_{CC}
- Supports **partial-power-down** with back drive protection (I_{off})
- High push-pull output drive strength:
 - $\pm 24\text{mA}$ at 3.3V
 - $\pm 8\text{mA}$ at 2.3V
 - $\pm 4\text{mA}$ at 1.65V
- Maximum propagation delay of 20ns at 3.3V
- Latch-up performance exceeds 100mA per JESD78

2 Applications

- [Increase the number of inputs on a microcontroller](#)
- Read in board revision

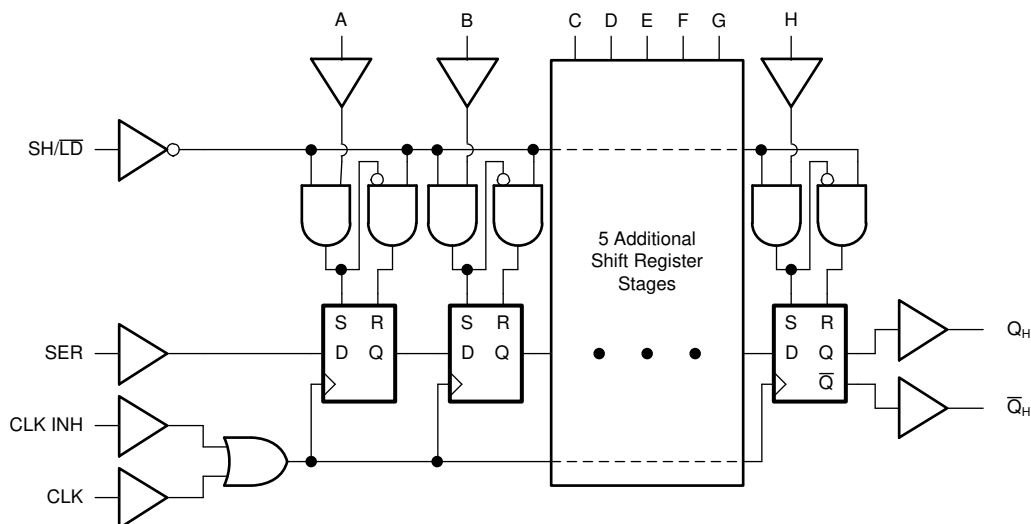
3 Description

The SN74LVC165A contains one 8-bit parallel-load shift register. Data is loaded asynchronously using the shift or load (SH/ $\overline{\text{LD}}$) select pin. The device includes a serial (SER) input to allow for daisy chaining, and a standard (Q_H) and inverted (\overline{Q}_H) output.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE (NOM) ⁽³⁾
SN74LVC165A	BQB (WQFN, 16)	3.5mm × 2.5mm	3.5mm × 2.5mm
	D (SOIC, 16)	9.9mm × 6mm	9.9mm × 3.9mm
	PW (TSSOP, 16)	5mm × 6.4mm	5mm × 4.4mm

- (1) For more information, see [Section 11](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable
- (3) The body size (length × width) is a nominal value and does not include pins.



Functional Diagram



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4 Pin Configuration and Functions

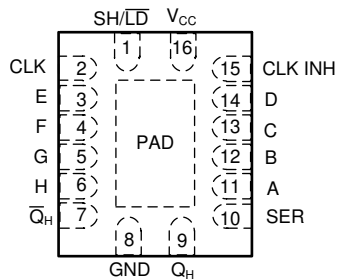


Figure 4-1. BQB Package, 16-Pin WQFN (Top View)

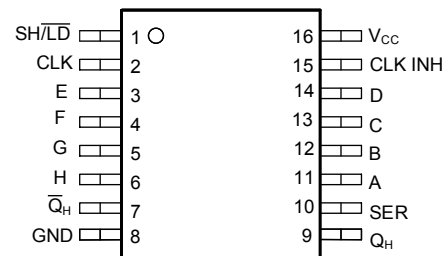


Figure 4-2. DYY or PW Package, 16-Pin VSSOP or TSSOP (Top View)

Table 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
SH/LD	1	I	Enable shifting when input is high, load data when input is low
CLK	2	I	Clock, rising edge triggered
E	3	I	Parallel input E
F	4	I	Parallel input F
G	5	I	Parallel input G
H	6	I	Parallel input H
\bar{Q}_H	7	O	Inverted serial output
GND	8	G	Ground
Q_H	9	O	Serial output
SER	10	I	Serial input
A	11	I	Parallel input A
B	12	I	Parallel input B
C	13	I	Parallel input C
D	14	I	Parallel input D
CLK INH	15	I	Clock inhibit input
V _{CC}	16	P	Positive supply
Thermal Pad ⁽²⁾		—	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.

(1) Signal Types: I = Input, O = Output, I/O = Input or Output, P = Power, G = Ground.

(2) Only applies to the BQB package

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage range	-0.5	6.5	V
V _I	Input voltage range ⁽²⁾	-0.5	6.5	V
V _O	Output voltage range ⁽²⁾	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0 V		-50 mA
I _{OK}	Output clamp current	V _O < 0 V		-50 mA
I _O	Continuous output current			±50 mA
I _O	Continuous output current through V _{CC} or GND			±100 mA
T _J	Junction temperature	-65	150	°C
T _{stg}	Storage temperature	-65	150	°C
P _{tot}	Power dissipation ^{(3) (4)}			500 mW

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) For the PW package: above 79°C, the value of P_{tot} derates linearly with 7.1mW/°C.
- (4) For the DYY package: above 52°C, the value of P_{tot} derates linearly with 5.1mW/°C.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
V _{CC}	Supply voltage	Operating	1.1	3.6	V
V _I	Input voltage	0	5.5	V	
V _O	Output voltage	(High or low state)	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.8 V			-4
		V _{CC} = 2.3 V			-8
		V _{CC} = 2.7 V			-12
		V _{CC} = 3 V			-24
I _{OL}	Low-level output current	V _{CC} = 1.8 V			4
		V _{CC} = 2.3 V			8
		V _{CC} = 2.7 V			12
		V _{CC} = 3 V			24
Δt/Δv	Input transition rise or fall rate			10	ns/V
T _A	Operating free-air temperature	-40	125	°C	

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC ⁽¹⁾						UNIT
		R _{θJA}	R _{θJC(top)}	R _{θJB}	Ψ _{JT}	Ψ _{JB}	R _{θJC(bot)}	
PW (TSSOP)	16	141.8	74	87.1	22.3	86.6	-	°C/W
DYY (SOT-23-THN)	16	196.3	117.4	122.9	22.3	122.7	-	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
V _{OH}	I _{OH} = -100μA	1.1V to 3.6V	V _{CC} - 0.2	V _{CC} - 0.01		V
V _{OH}	I _{OH} = -4mA	1.65V	1.2			V
V _{OH}	I _{OH} = -8mA	2.3V	1.75			V
V _{OH}	I _{OH} = -12mA	2.7V	2.2			V
V _{OH}	I _{OH} = -12mA	3V	2.4			V
V _{OH}	I _{OH} = -24mA	3V	2.2			V
V _{OL}	I _{OL} = 100μA	1.1V to 3.6V		0.01	0.2	V
V _{OL}	I _{OL} = 4mA	1.2V			0.45	V
V _{OL}	I _{OL} = 8mA	1.5V			0.7	V
V _{OL}	I _{OL} = 12mA	1.65V			0.4	V
V _{OL}	I _{OL} = 24mA	3.6V			0.55	V
I _I	V _I = V _{CC} or GND	3.6V			±5	μA
I _{off}	V _I or V _O = V _{CC}	0V			±10	μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	3.6V			40	μA
ΔI _{CC}	One input at V _{CC} - 0.6V, other inputs at V _{CC} or GND	2.7V to 3.6V			5000	μA
C _I	V _I = V _{CC} or GND	3.3V		4.9		pF
C _O	V _O = V _{CC} or GND	3.3V		6.3		pF
C _{PD}	f = 10MHz	1.8V		12		pF
		2.5V		15		pF
		3.3V		17		pF

5.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V _{CC}	-40°C to 125°C		UNIT
				MIN	MAX	
f _{clock}	Clock frequency		1.2V ± 0.1V	59		MHz
			1.5V ± 0.15V	64		
			1.8V ± 0.15V	64		
			2.5V ± 0.2V	100		
			3.3V ± 0.3V	104		
t _W	Pulse duration	SH/LD low	1.2V ± 0.1V	6.9		ns
t _W	Pulse duration	CLK high or low	1.2V ± 0.1V	7		ns
t _{SU}	Setup time	SH/LD high before CLK↑	1.2V ± 0.1V	16.5		ns

5.6 Timing Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V _{CC}	-40°C to 125°C		UNIT
				MIN	MAX	
t _{SU}	Setup time	SER before CLK↑	1.2V ± 0.1V	10.1		ns
t _{SU}	Setup time	CLK INH low before CLK↑	1.2V ± 0.1V	1		ns
t _{SU}	Setup time	CLK INH high before CLK↑	1.2V ± 0.1V	1		ns
t _{SU}	Setup time	Data before SH/ $\overline{\text{LD}}$ ↓	1.2V ± 0.1V	10		ns
t _{SU}	Setup time	Data before CLK↑	1.2V ± 0.1V	10		ns
t _H	Hold time	SER data after CLK↑	1.2V ± 0.1V	0.4		ns
t _H	Hold time	PAR data after SH/ $\overline{\text{LD}}$ ↓	1.2V ± 0.1V	1.8		ns
t _H	Hold time	SH/ $\overline{\text{LD}}$ high after CLK↑	1.2V ± 0.1V	0		ns
t _H	Hold time	CLK INH high after CLK↑	1.2V ± 0.1V	0.4		ns
t _H	Hold time	Data after CLK↑	1.2V ± 0.1V	1		ns
t _W	Pulse duration	SH/ $\overline{\text{LD}}$ low	1.5V ± 0.15V	6.9		ns
t _W	Pulse duration	CLK high or low	1.5V ± 0.15V	7		ns
t _{SU}	Setup time	SH/ $\overline{\text{LD}}$ high before CLK↑	1.5V ± 0.15V	10		ns
t _{SU}	Setup time	SER before CLK↑	1.5V ± 0.15V	10.1		ns
t _{SU}	Setup time	CLK INH low before CLK↑	1.5V ± 0.15V	1		ns
t _{SU}	Setup time	CLK INH high before CLK↑	1.5V ± 0.15V	1		ns
t _{SU}	Setup time	Data before SH/ $\overline{\text{LD}}$ ↓	1.5V ± 0.15V	10		ns
t _{SU}	Setup time	Data before CLK↑	1.5V ± 0.15V	10		ns
t _H	Hold time	SER data after CLK↑	1.5V ± 0.15V	1.2		ns
t _H	Hold time	PAR data after SH/ $\overline{\text{LD}}$ ↓	1.5V ± 0.15V	1.9		ns
t _H	Hold time	SH/ $\overline{\text{LD}}$ high after CLK↑	1.5V ± 0.15V	1		ns
t _H	Hold time	CLK INH high after CLK↑	1.5V ± 0.15V	0.6		ns
t _H	Hold time	Data after CLK↑	1.5V ± 0.15V	0.5		ns
t _W	Pulse duration	SH/ $\overline{\text{LD}}$ low	1.8V ± 0.15V	6.9		ns
t _W	Pulse duration	CLK high or low	1.8V ± 0.15V	7		ns
t _{SU}	Setup time	SH/ $\overline{\text{LD}}$ high before CLK↑	1.8V ± 0.15V	8		ns
t _{SU}	Setup time	SER before CLK↑	1.8V ± 0.15V	10.1		ns
t _{SU}	Setup time	CLK INH low before CLK↑	1.8V ± 0.15V	1		ns
t _{SU}	Setup time	CLK INH high before CLK↑	1.8V ± 0.15V	1		ns
t _{SU}	Setup time	Data before SH/ $\overline{\text{LD}}$ ↓	1.8V ± 0.15V	10		ns
t _{SU}	Setup time	Data before CLK↑	1.8V ± 0.15V	8		ns
t _H	Hold time	SER data after CLK↑	1.8V ± 0.15V	0.2		ns
t _H	Hold time	PAR data after SH/ $\overline{\text{LD}}$ ↓	1.8V ± 0.15V	0.8		ns
t _H	Hold time	SH/ $\overline{\text{LD}}$ high after CLK↑	1.8V ± 0.15V	0		ns
t _H	Hold time	CLK INH high after CLK↑	1.8V ± 0.15V	0.3		ns
t _H	Hold time	Data after CLK↑	1.8V ± 0.15V	1		ns
t _W	Pulse duration	SH/ $\overline{\text{LD}}$ low	2.5V ± 0.2V	5.4		ns
t _W	Pulse duration	CLK high or low	2.5V ± 0.2V	4.5		ns
t _{SU}	Setup time	SH/ $\overline{\text{LD}}$ high before CLK↑	2.5V ± 0.2V	4.5		ns
t _{SU}	Setup time	SER before CLK↑	2.5V ± 0.2V	5.9		ns
t _{SU}	Setup time	CLK INH low before CLK↑	2.5V ± 0.2V	1		ns
t _{SU}	Setup time	CLK INH high before CLK↑	2.5V ± 0.2V	1		ns

5.6 Timing Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V _{CC}	-40°C to 125°C		UNIT
				MIN	MAX	
t _{SU}	Setup time	Data before SH/ $\overline{\text{LD}}\downarrow$	2.5V ± 0.2V	6.9		ns
t _{SU}	Setup time	Data before CLK \uparrow	2.5V ± 0.2V	4.5		ns
t _H	Hold time	SER data after CLK \uparrow	2.5V ± 0.2V	0.5		ns
t _H	Hold time	PAR data after SH/ $\overline{\text{LD}}\downarrow$	2.5V ± 0.2V	0		ns
t _H	Hold time	SH/ $\overline{\text{LD}}$ high after CLK \uparrow	2.5V ± 0.2V	0.1		ns
t _H	Hold time	CLK INH high after CLK \uparrow	2.5V ± 0.2V	0.3		ns
t _H	Hold time	Data after CLK \uparrow	2.5V ± 0.2V	1.5		ns
t _W	Pulse duration	SH/ $\overline{\text{LD}}$ low	3.3V ± 0.3V	4.3		ns
t _W	Pulse duration	CLK high or low	3.3V ± 0.3V	4.3		ns
t _{SU}	Setup time	SH/ $\overline{\text{LD}}$ high before CLK \uparrow	3.3V ± 0.3V	3.5		ns
t _{SU}	Setup time	SER before CLK \uparrow	3.3V ± 0.3V	4		ns
t _{SU}	Setup time	CLK INH low before CLK \uparrow	3.3V ± 0.3V	1		ns
t _{SU}	Setup time	CLK INH high before CLK \uparrow	3.3V ± 0.3V	1		ns
t _{SU}	Setup time	Data before SH/ $\overline{\text{LD}}\downarrow$	3.3V ± 0.3V	5.3		ns
t _{SU}	Setup time	Data before CLK \uparrow	3.3V ± 0.3V	2.9		ns
t _H	Hold time	SER data after CLK \uparrow	3.3V ± 0.3V	0.5		ns
t _H	Hold time	PAR data after SH/ $\overline{\text{LD}}\downarrow$	3.3V ± 0.3V	0		ns
t _H	Hold time	SH/ $\overline{\text{LD}}$ high after CLK \uparrow	3.3V ± 0.3V	0.2		ns
t _H	Hold time	CLK INH high after CLK \uparrow	3.3V ± 0.3V	0.5		ns
t _H	Hold time	Data after CLK \uparrow	3.3V ± 0.3V	1.5		ns

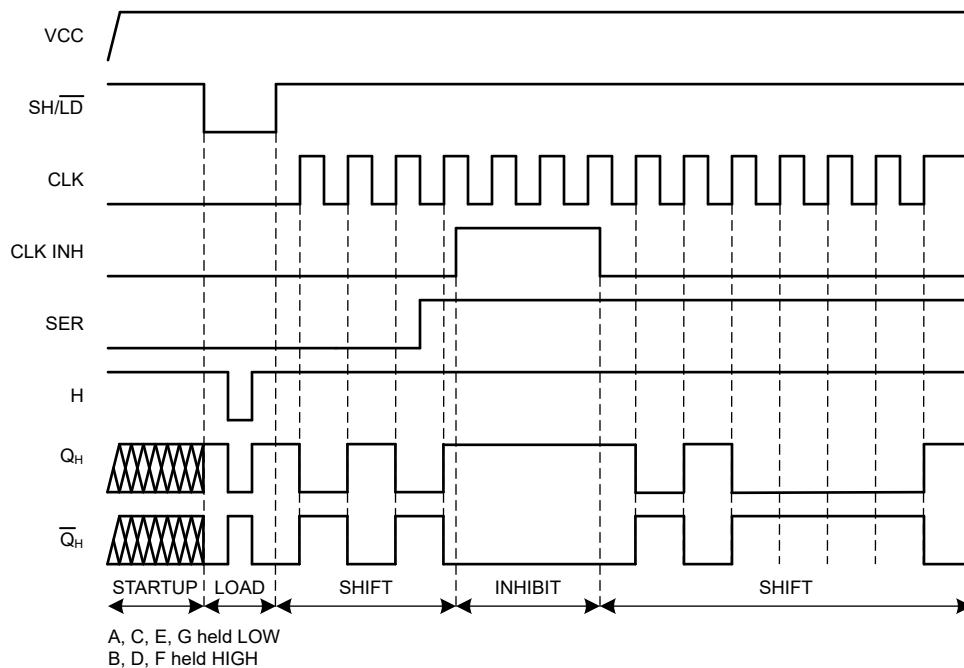


Figure 5-1. Timing Diagram

5.7 Switching Characteristics

over operating free-air temperature range(unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V _{CC}	-40°C to 125°C			UNIT
					MIN	TYP	MAX	
t _{pd}	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 15pF	1.2V ± 0.1V	1	15.4	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 15pF	1.2V ± 0.1V	1	17	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 15pF	1.2V ± 0.1V	1	21.2	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 30pF	1.2V ± 0.1V	1	16.3	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 30pF	1.2V ± 0.1V	1	17.7	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 30pF	1.2V ± 0.1V	1	22.2	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 50pF	1.2V ± 0.1V	1	17.5	32.8	ns
	H	Q _H or \overline{Q}_H	C _L = 50pF	1.2V ± 0.1V	1	18.8	38.5	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 50pF	1.2V ± 0.1V	1	23.5	45.4	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 15pF	1.5V ± 0.15V	1	8.6	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 15pF	1.5V ± 0.15V	1	9.7	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 15pF	1.5V ± 0.15V	1	11.7	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 30pF	1.5V ± 0.15V	1	9.2	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 30pF	1.5V ± 0.15V	1	10.2	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 30pF	1.5V ± 0.15V	1	12.3	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 50pF	1.5V ± 0.15V	1	9.9	32.8	ns
	H	Q _H or \overline{Q}_H	C _L = 50pF	1.5V ± 0.15V	1	10.9	41.5	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 50pF	1.5V ± 0.15V	1	13	45.4	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 15pF	1.8V ± 0.15V	1	6.7	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 15pF	1.8V ± 0.15V	1	7.6	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 15pF	1.8V ± 0.15V	1	9.2	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 30pF	1.8V ± 0.15V	1	6.8	27.6	ns
	H	Q _H or \overline{Q}_H	C _L = 30pF	1.8V ± 0.15V	1	7.6	36.3	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 30pF	1.8V ± 0.15V	1	9	40.2	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 50pF	1.8V ± 0.15V	1	8	32.8	ns
	H	Q _H or \overline{Q}_H	C _L = 50pF	1.8V ± 0.15V	1	8.8	41.5	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 50pF	1.8V ± 0.15V	1	10.4	45.4	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 15pF	2.5V ± 0.2V	1	4.5	16	ns
	H	Q _H or \overline{Q}_H	C _L = 15pF	2.5V ± 0.2V	1	5.1	21	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 15pF	2.5V ± 0.2V	1	6.1	23.8	ns
	CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 30pF	2.5V ± 0.2V	1	4.5	16	ns
	H	Q _H or \overline{Q}_H	C _L = 30pF	2.5V ± 0.2V	1	5	21	ns
	SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 30pF	2.5V ± 0.2V	1	5.9	23.8	ns
CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 50pF	2.5V ± 0.2V	1	5.5	20	ns	
H	Q _H or \overline{Q}_H	C _L = 50pF	2.5V ± 0.2V	1	6.1	25	ns	
SH/ \overline{LD}	Q _H or \overline{Q}_H	C _L = 50pF	2.5V ± 0.2V	1	7.1	27.7	ns	
CLK or CLK INH	Q _H or \overline{Q}_H	C _L = 15pF	3.3V ± 0.3V	1	3.6	11.2	ns	
H	Q _H or \overline{Q}_H	C _L = 15pF	3.3V ± 0.3V	1	4.1	14.5	ns	

5.7 Switching Characteristics (continued)

over operating free-air temperature range(unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V _{CC}	-40°C to 125°C			UNIT
					MIN	TYP	MAX	
t _{pd}	SH/LD	Q _H or \bar{Q}_H	C _L = 15pF	3.3V ± 0.3V	1	4.8	16.6	ns
	CLK or CLK INH	Q _H or \bar{Q}_H	C _L = 30pF	3.3V ± 0.3V	1	3.9	11.2	ns
	H	Q _H or \bar{Q}_H	C _L = 30pF	3.3V ± 0.3V	1	4.4	14.5	ns
	SH/LD	Q _H or \bar{Q}_H	C _L = 30pF	3.3V ± 0.3V	1	5.1	16.6	ns
	CLK or CLK INH	Q _H or \bar{Q}_H	C _L = 50pF	3.3V ± 0.3V	1	4.2	14.5	ns
	H	Q _H or \bar{Q}_H	C _L = 50pF	3.3V ± 0.3V	1	4.6	17.8	ns
	SH/LD	Q _H or \bar{Q}_H	C _L = 50pF	3.3V ± 0.3V	1	5.3	19.9	ns

5.8 Noise Characteristics

V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}			0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}	-0.8	-0.3		V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}	2.2	3.3		V
V _{IH(D)}	High-level dynamic input voltage	2.0			V
V _{IL(D)}	Low-level dynamic input voltage			0.8	V

5.9 Typical Characteristics

T_A = 25°C (unless otherwise noted)

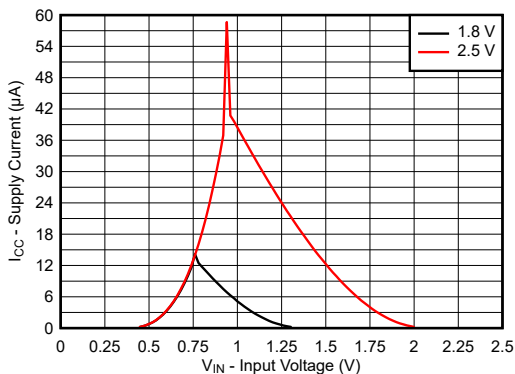


Figure 5-2. Supply Current Across Input Voltage 1.8V and 2.5V Supply

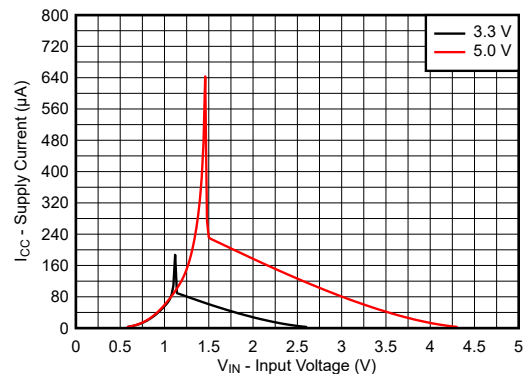


Figure 5-3. Supply Current Across Input Voltage 3.3V and 5.0V Supply

5.9 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

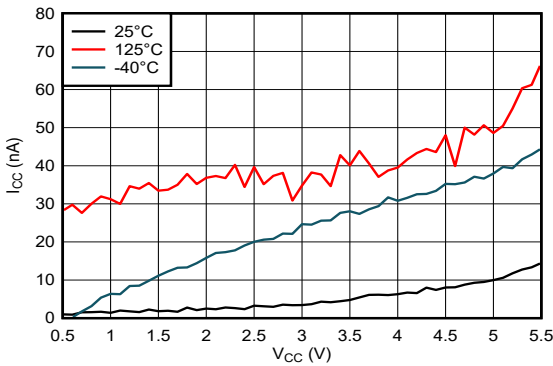


Figure 5-4. Supply Current Across Supply Voltage

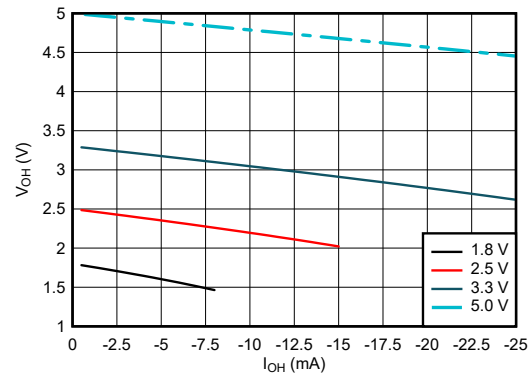


Figure 5-5. Output Voltage vs Current in HIGH State

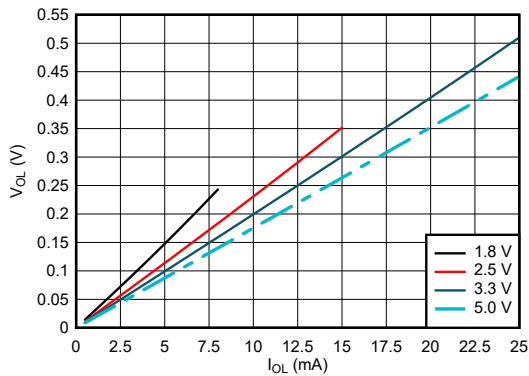


Figure 5-6. Output Voltage vs Current in LOW State

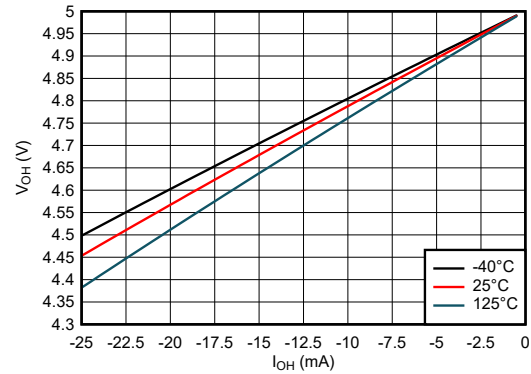


Figure 5-7. Output Voltage vs Current in HIGH State; 5V Supply

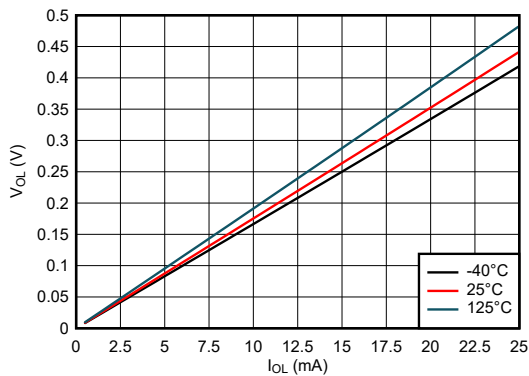


Figure 5-8. Output Voltage vs Current in LOW State; 5V Supply

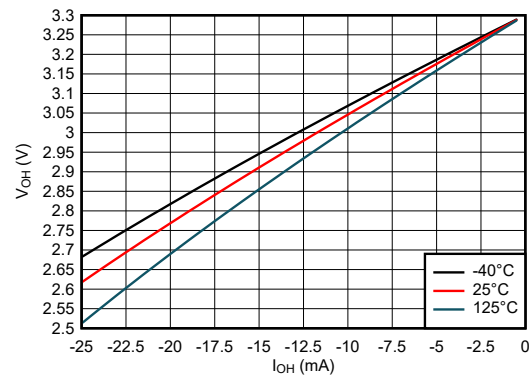


Figure 5-9. Output Voltage vs Current in HIGH State; 3.3V Supply

5.9 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

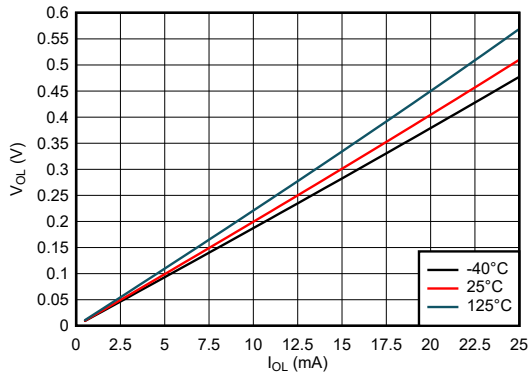


Figure 5-10. Output Voltage vs Current in LOW State; 3.3V Supply

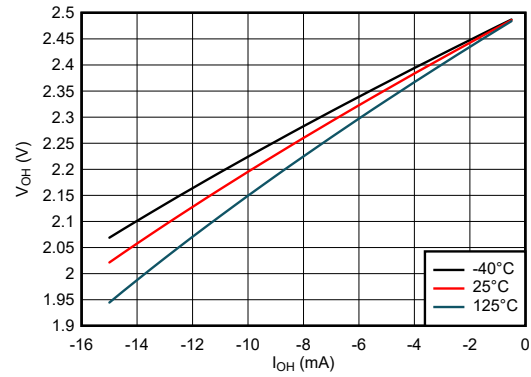


Figure 5-11. Output Voltage vs Current in HIGH State; 2.5V Supply

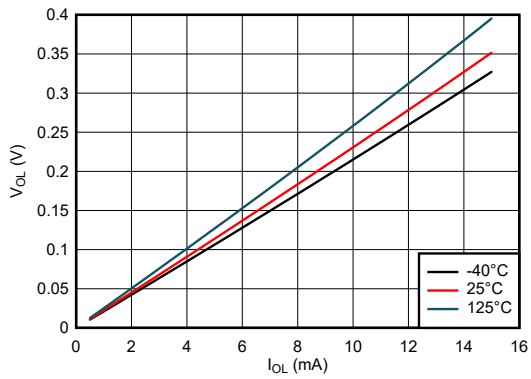


Figure 5-12. Output Voltage vs Current in LOW State; 2.5V Supply

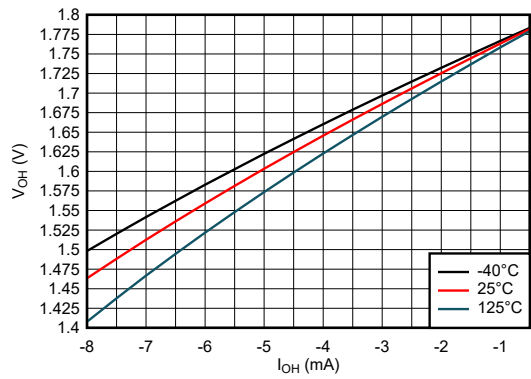


Figure 5-13. Output Voltage vs Current in HIGH State; 1.8V Supply

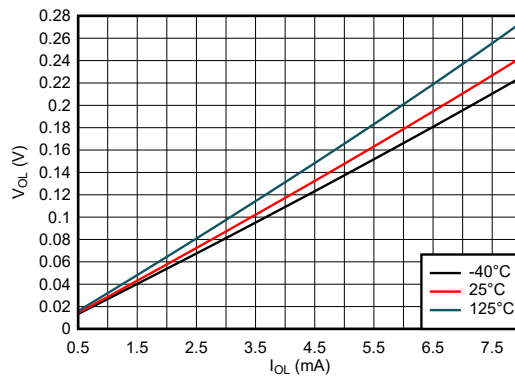


Figure 5-14. Output Voltage vs Current in LOW State; 1.8V Supply

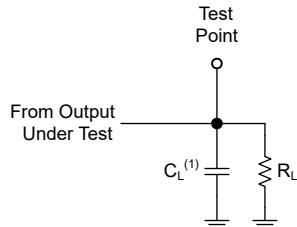
6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{MHz}$, $Z_O = 50\Omega$, $t_f \leq 2.5\text{ns}$.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured individually with one input transition per measurement.

V_{CC}	V_t	R_L	C_L	ΔV
$1.2\text{V} \pm 0.1\text{V}$	$V_{CC}/2$	$2\text{k}\Omega$	15pF	0.1V
$1.5\text{V} \pm 0.12\text{V}$	$V_{CC}/2$	$2\text{k}\Omega$	15pF	0.1V
$1.8\text{V} \pm 0.15\text{V}$	$V_{CC}/2$	$1\text{k}\Omega$	30pF	0.15V
$2.5\text{V} \pm 0.2\text{V}$	$V_{CC}/2$	500Ω	30pF	0.15V
2.7V	1.5V	500Ω	50pF	0.3V
$3.3\text{V} \pm 0.3\text{V}$	1.5V	500Ω	50pF	0.3V



(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs

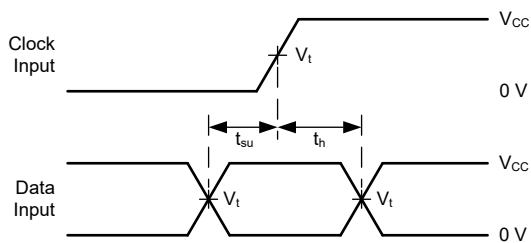


Figure 6-3. Voltage Waveforms, Setup and Hold Times

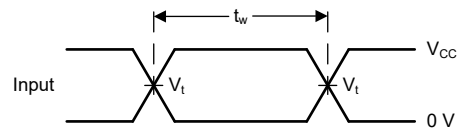
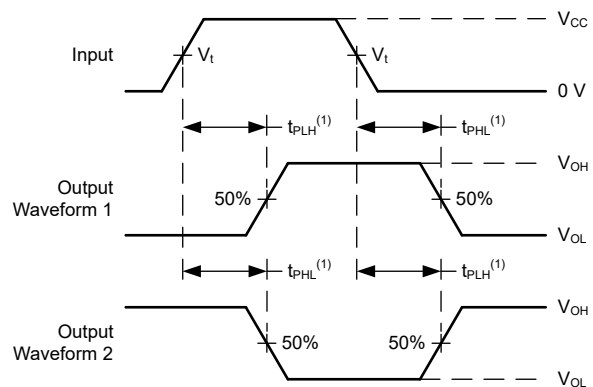
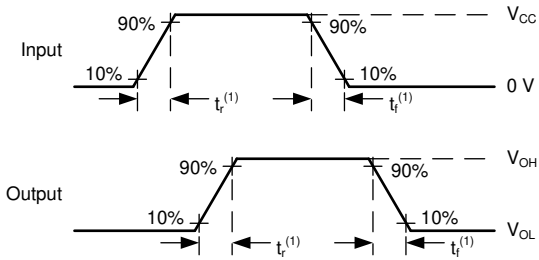


Figure 6-2. Voltage Waveforms, Pulse Duration



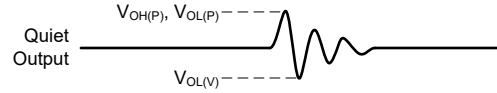
(1) The greater between t_{pLH} and t_{pHL} is the same as t_{pd} .

Figure 6-4. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

Figure 6-5. Voltage Waveforms, Input and Output Transition Times



Noise values measured with all other outputs simultaneously switching.

Figure 6-6. Voltage Waveforms, Noise

7 Detailed Description

7.1 Overview

The SN74LVC165A device is an 8-bit parallel-load shift register that, when clocked, shifts the data toward a serial (Q_H) output. Parallel-in access to each stage is provided by eight individual direct data (A–H) inputs that are enabled by a low level at the shift/load (SH/\overline{LD}) input. The SN74LVC165A device also features a clock-inhibit (CLK INH) function and a complementary serial (\overline{Q}_H) output.

Clocking is accomplished by a low-to-high transition of the clock (CLK) input while SH/\overline{LD} is held high and CLK INH is held low. The functions of CLK and CLK INH are interchangeable. Because a low CLK and a low-to-high transition of CLK INH also accomplishes clocking, CLK INH must be changed to the high level only while CLK is high. Parallel loading is inhibited when SH/\overline{LD} is held high. While SH/\overline{LD} is low, the parallel inputs to the register are enabled independently of the levels of the CLK, CLK INH, or SER inputs.

7.2 Functional Block Diagram

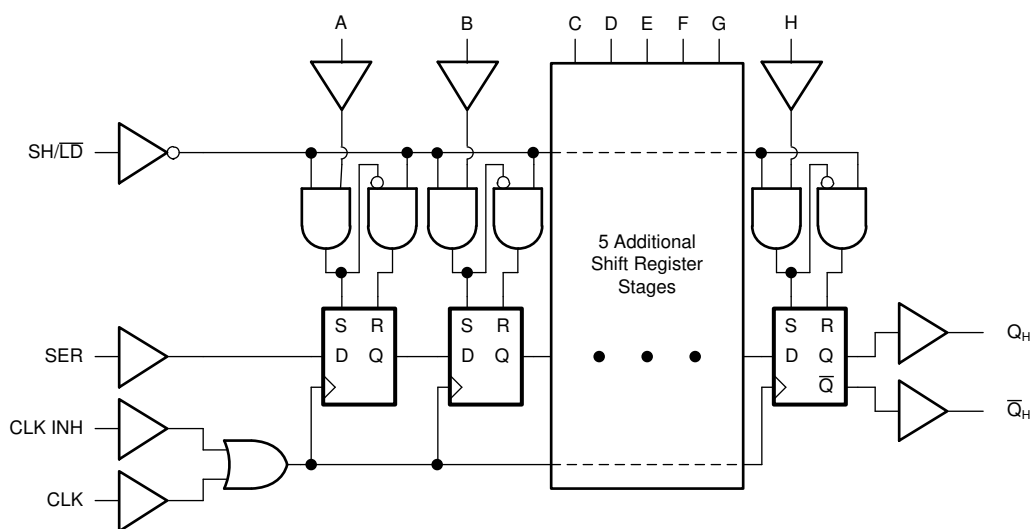


Figure 7-1. Logic Diagram (Positive Logic) for SN74LVC165A

7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

7.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

7.3.4 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in [Implications of Slow or Floating CMOS Inputs](#).

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10k Ω resistor, however, is recommended and will typically meet all requirements.

7.3.5 Clamp Diode Structure

As [Figure 7-2](#) shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

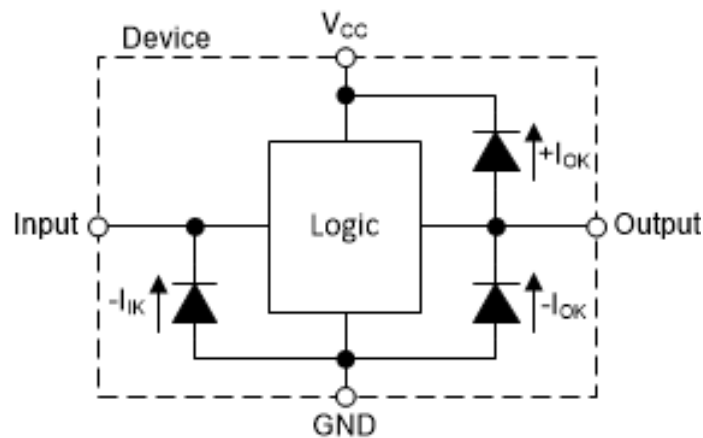


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1 and Table 7-2 list the functional modes of the SN74LVC165A.

Table 7-1. Operating Mode Table

INPUTS ⁽¹⁾			FUNCTION
SH/LD	CLK	CLK INH	
L	X	X	Parallel load ⁽²⁾
H	H	X	No change
H	X	H	No change
H	L	↑	Shift ⁽³⁾
H	↑	L	Shift ⁽³⁾

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care, ↑ = Low to High transition
- (2) Parallel load : Values at inputs A through H are loaded to respective internal registers.
- (3) Shift : Content of each internal register shifts towards serial output Q_H. Data at SER is shifted into the first register.

Table 7-2. Output Function Table

INTERNAL REGISTERS ^{(1) (2)}		OUTPUTS ⁽³⁾	
A — G	H	Q	\bar{Q}
X	L	L	H
X	H	H	L

- (1) Internal registers refer to the shift registers inside the device. These values are set by either loading data from the parallel inputs, or by clocking data in from the serial input.
- (2) H = High voltage level, L = Low voltage level, X = Don't care
- (3) H = Driving high, L = Driving low

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC165A is a parallel-input shift register, which can significantly reduce the number of required inputs on a system controller in some applications. Parallel data is loaded into the shift register, then the stored data can be loaded into a serial input of the system controller by clocking the shift register.

Multiple shift registers can be cascaded to provide more data inputs while still only using a single serial input to the system controller. This process is primarily limited by the required data input rate and timing characteristics of the selected shift register, as defined in the *Timing Characteristics* and *Switching Characteristics* tables.

An example block diagram is shown for using a single shift register in the *Typical Application Block Diagram*.

8.2 Typical Application

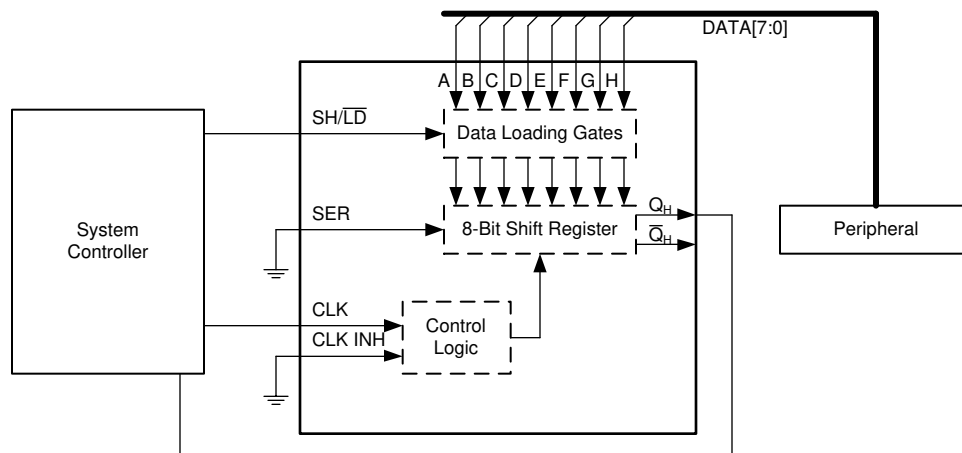


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVC165A plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LVC165A plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74LVC165A can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74LVC165A can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LVC165A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10k Ω resistor value is often used due to these factors.

The SN74LVC165A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.

2. Ensure the capacitive load at the output is $\leq 50\text{pF}$. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVC165A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)})\Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

8.2.3 Application Curve

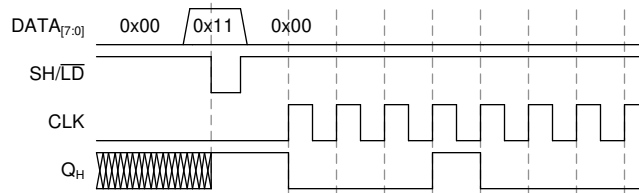


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

During startup, the power supply should ramp within the provided power-up ramp rate range in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For the SN74LVC165A, a $0.1\mu\text{F}$ bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of $0.1\mu\text{F}$ and $1\mu\text{F}$ are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

8.4.2 Layout Example

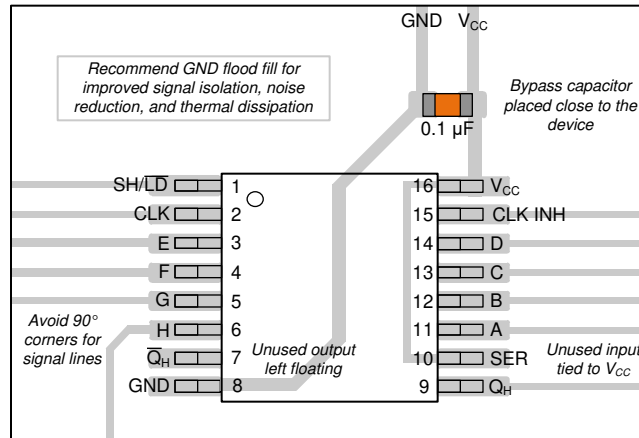


Figure 8-3. Example Layout for the SN74LVC165A in the PW Package

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

DATE	REVISION	NOTES
May 2024	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC165ABQBR	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC165A	Samples
SN74LVC165APWR	ACTIVE	TSSOP	PW	16	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LVC165	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC165A :

- Automotive : [SN74LVC165A-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

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